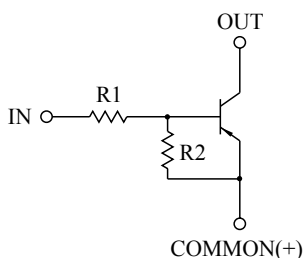


SWITCHING APPLICATION.
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

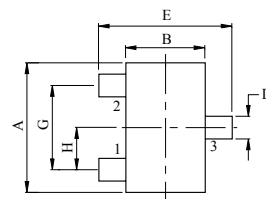
- With Built-in Bias Resistors
- Simplify Circuit Design
- Reduce a Quantity of Parts and Manufacturing Process
- High Packing Density.

EQUIVALENT CIRCUIT

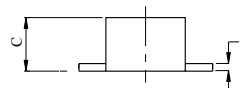


BIAS RESISTOR VALUES

TYPE NO.	R1(k Ω)	R2(k Ω)
KRA307E	10	47
KRA308E	22	47
KRA309E	47	22



DIM	MILLIMETERS
A	1.60 $\pm$ 0.10
B	0.85 $\pm$ 0.10
C	0.70 $\pm$ 0.10
D	0.27 $\pm$ 0.10/-0.05
E	1.60 $\pm$ 0.10
G	1.00 $\pm$ 0.10
H	0.50
J	0.13 $\pm$ 0.05



1. COMMON (EMITTER)
2. IN (BASE)
3. OUT (COLLECTOR)

ESM

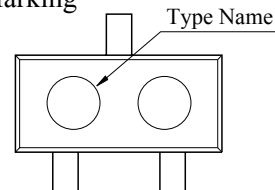
MAXIMUM RATING (Ta=25 $^{\circ}$ C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Output Voltage	KRA307E ~ 309E	V_O	-50	V
Input Voltage	KRA307E	V_I	-30, 6	V
	KRA308E		-40, 7	
	KRA309E		-40, 15	
Output Current	KRA307E ~ 309E	I_O	-100	mA
Power Dissipation		P_D	100	mW
Junction Temperature		T_j	150	$^{\circ}$ C
Storage Temperature Range		T_{stg}	-55 ~ 150	$^{\circ}$ C

MARK SPEC

TYPE	KRA307E	KRA308E	KRA309E
MARK	PH	PI	PJ

Marking



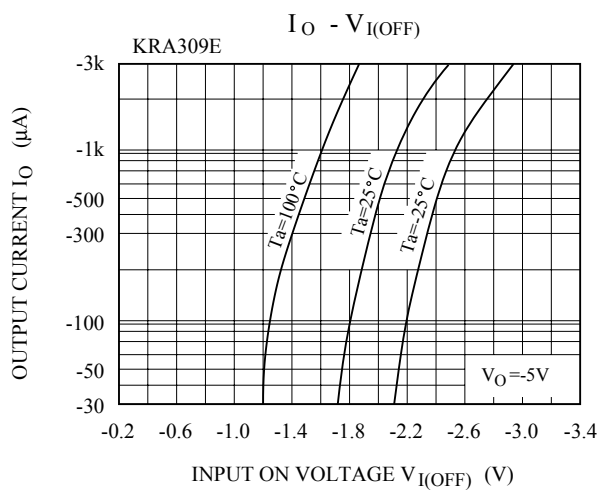
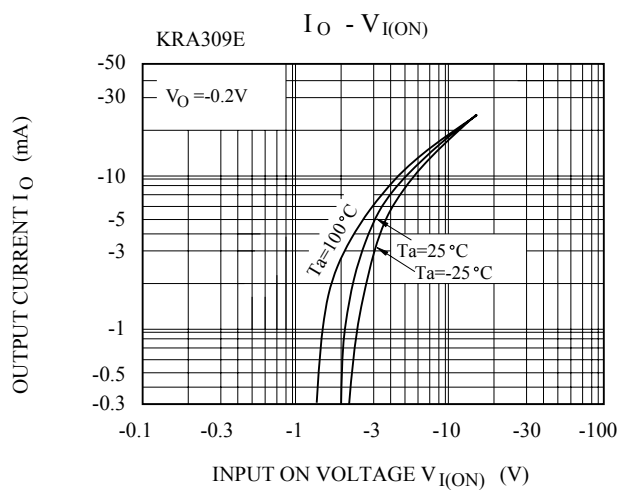
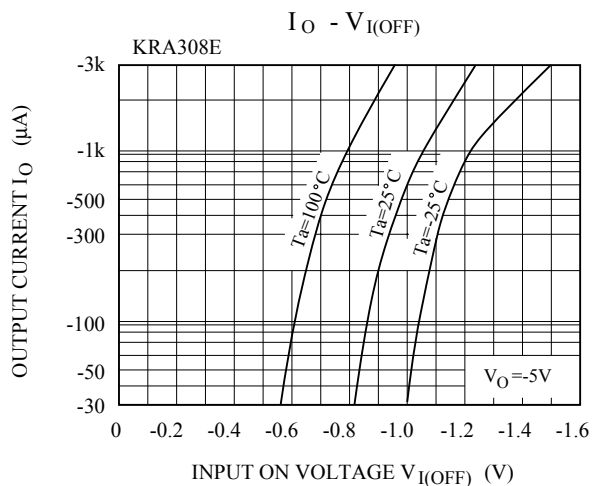
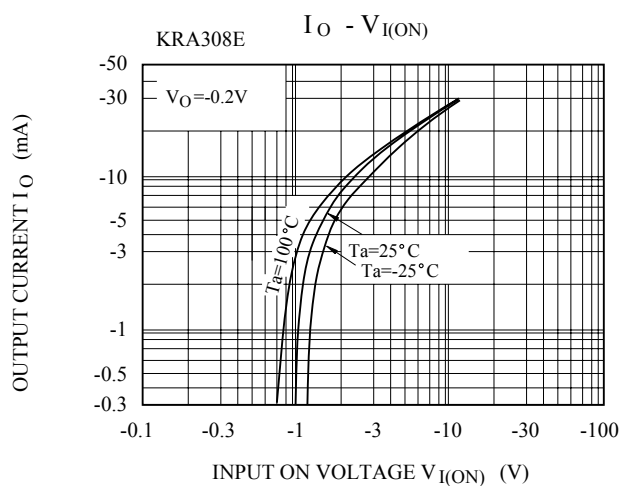
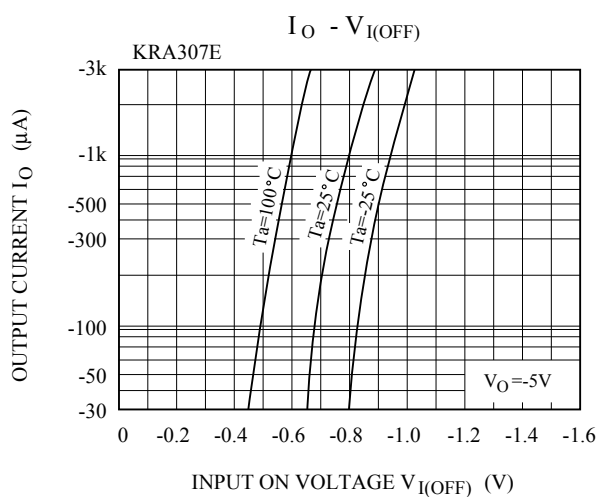
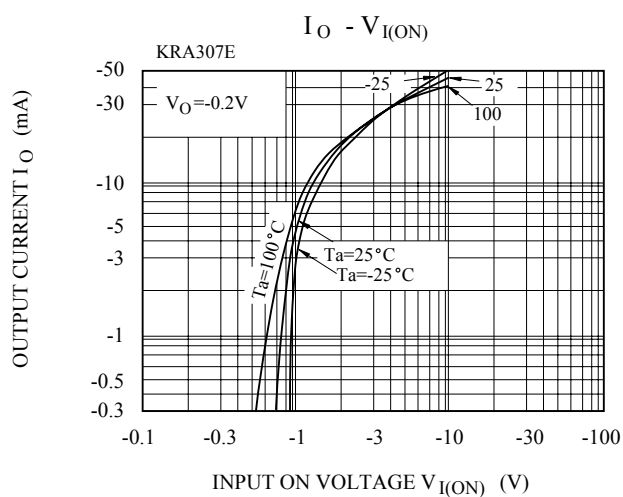
KRA307E~KRA309E

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT		
Output Cut-off Current		KRA307E ~ 309E	I _{O(OFF)}	V _O =-50V, V _I =0	-	-	-500	nA	
DC Current Gain	KRA307E	G _I	V _O =-5V, I _O =-10mA	80	150	-			
	KRA308E			80	150	-			
	KRA309E			70	140	-			
Output Voltage		KRA307E ~ 309E	V _{O(ON)}	I _O =-10mA, I _I =-0.5mA	-	-0.1	-0.3	V	
Input Voltage (ON)	KRA307E	V _{I(ON)}	V _O =-0.2V, I _O =-5mA	-	-1.2	-1.8	V		
	KRA308E			-	-1.8	-2.6			
	KRA309E			-	-3.0	-5.8			
Input Votlage (OFF)	KRA307E	V _{I(OFF)}	V _O =-5V, I _O =-0.1mA	-0.5	-0.75	-	V		
	KRA308E			-0.6	-0.88	-			
	KRA309E			-1.5	-1.82	-			
Transition Frequency		KRA307E ~ 309E	f _T *	V _O =-10V, I _O =-5mA	-	200	-	MHz	
Input Current		KRA307E	I _I	V _I =-5V	-	-	-0.88	mA	
		KRA308E			-	-	-0.36		
		KRA309E			-	-	-0.16		
Switching Time	Rise Time	KRA307E	t _r	V _O =-5V, V _{IN} =-5V R _L =1kΩ	-	0.07	-	μS	
		KRA308E			-	0.20	-		
		KRA309E			-	0.38	-		
	Storage Time	KRA307E			t _{stg}	-	1.1		-
		KRA308E				-	1.3		-
		KRA309E				-	0.7		-
	Fall Time	KRA307E			t _f	-	0.35		-
		KRA308E				-	0.4		-
		KRA309E				-	0.48		-

Note : * Characteristic of Transistor Only.

KRA307E~KRA309E



KRA307E~KRA309E

